LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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APPLICANT(S): Kuang Chien et al.

EXAMINER INITIAL		DOCUMENT NUMBER Numbar-Kind Code (If known)	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
W //	B1	5,920,766	July 6, 1999	Floyd		
1	B2	5,858,855	January 12, 1999	Kobayashi		
1	B3	5,854,090	December 29, 1998	lwai et al.		
	B4	5,233,216	August 3, 1993	Inoue et al.		
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FOREIGN PATENT DOCUMENTS TRANSLATION CLASS/ **DOCUMENT EXAMINER** YES OR NO **SUBCLASS** INITIAL NUMBER DATE COUNTRY Number-Kind Code (if known) EP 1 246 238 A2 October 2, 2002 **EPO B5** JP 10-12506 January 16, 1998 Japan **B6**

EXAMINER INITIAL	OTHER ART — NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.		
125	B7	Copy of International Search Report from corresponding PCT patent application number PCT/US2004/031254.	
	B8	K.L. Chang, G.W. Pickrell, K.Y. Cheng and K.C. Hsieh, Wafer Bonding With Low-Temperature- Grown (Ga,P) as an Adhesive Material, pgs. 906-910, Institute of Physics Publishing, Semiconductor Science and Technology, 2004	
	89	K.D. Choquette, K.M. Geib, B. Roberds, H.Q. Hou, R.D. Twesten and B.E. Hammons, Short Wavelength Bottom-Emitting Vertical Cavity Lasers Fabricated Using Wafer Bonding, pgs. 1404-1405, IEEE, Electronic Letters, Vol. 34, No. 14, July 9, 1998.	
	B10	K. Mori, K. Tokutome and S. Sugou, Low-Threshold Pulsed Operation of Long-wavelength Lasers on Si Fabricated By Direct Bonding, pgs. 284-285, IEEE Electronic Letters, Vol. 31, No. 4, February 16, 1995.	

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EXAMINER V	4 Mil	DATE CONSIDERED DI 12/06

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.